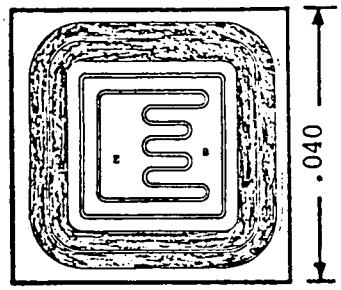
PRELIMINARY DATA SHEET 5-8-85

X00220

STX625 CHIP

HIGH VOLTAGE PNP TRANSISTOR CHIP



Contact Area: .005 x .005

CONTACT METALLIZATION

Base/Emitter: > 30,000 Å Aluminum

Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 2 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS	TYPE	MIN.	MAX.	UNIT
BV_{CEO}	IC = 1 mA (pulsed)		450		Vdc
BV_{CBO}	IC = 100 uA		500		Vdc
BV_{CER}	IC = 100 uA, RBE= 5 K Ohm		500		Vdc
BV_{EBO}	IE = 20 uA				Vdc
I_{EBO}	VEB = 4 V			250	n Adc
I_{CBO}	VCB = 500 V			500	n Adc
h_{FE}	VCE = 10 V, IC = 1 mA		20	200	
h_{FE}	VCE = 10 V, IC = 25 mA		40	250	
h_{FE}	VCE = 15 V, IC= 100 mA		20	200	
$V_{BE(SAT)}$	IC = 25 mA, IB= 2.5 mA			1.0	Vdc
$V_{CE(SAT)}$	IC = 25 mA, IB= 2.5 mA			3.0	Vdc
C_{OB}	VCB = 15 V			20	pf
f_T	VCE = 20 V, IC = 10 mA f = 5 MHz		20		MHz

Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

SSDI SOLID STATE DEVICES, INC.

P.O. Box 577, La Mirada, California, 90637-0577 TWX 910-583-4807

14830 Valley View Avenue, La Mirada, California, 90638 (213) 921-9660